**WHAT IS CLAIMED IS:**

1. A device measuring a physical state of a material by spectrum, comprising:

- a first action path where a material to be measured and the other material are contained in;
- a detecting unit detecting a spectrum emitted from the other material in the plasma state; and
- a processing unit obtaining a deposition state relating to the material to be measured based on the spectrum and at least one of a relationship of chemical reaction formula and a relationship of supplied mole quantity between the other material and the material to be measured;
- a control unit connected to the processing unit for controlling a reaction condition of the material to be measured based on the spectrum; and a memory unit connected to the processing unit for storing the spectrum, a reaction condition, a theoretical state, an actual state, a default state, an adjustment parameter; wherein an artificial intelligence is used for a big data calculation and operating the controlling unit and the detecting unit detecting a physic state based on the big data calculation through the spectrum, the reaction condition, the theoretical state, the actual state, the default state, the adjustment parameter or at least a combination of the two.

2. A device measuring a physical state of a material by spectrum as mentioned in claim 1, wherein the spectrum in the first action path is detected by the detecting unit.

3. A device measuring a physical state of a material by spectrum of claim 1, wherein the first action path is communicated with a second action path, at least part of the material to be measured comes from the second action path, and the spectrum in the second action path is detected by the detecting unit.

4. A device measuring a physical state of a material by spectrum as mentioned in claim 1, wherein the first action path is communicated with a second action path via a tube, at least parts of the material to be measured come from the second action path via the tube, and the spectrum in the tube can be detected by the detecting unit.

5. A device measuring a physical state of a material by spectrum as mentioned in claim 1, wherein at least parts of the material to be measured are in a plasma state.

6. A method measuring a physical state of a material by spectrum, comprising:
detecting a spectrum emitted from the other material in the plasma state; and
obtaining a deposition state relating to a material to be measured based on the spectrum and at least one of a relationship of chemical reaction formula and a relationship of supplied mole quantity between the other material and the material to be measured;
controlling a reaction condition of the material to be measured based on the spectrum based on a spectrum variation of the other material;
storing the spectrum, a reaction condition, a theoretical state, an actual state, a default state, an adjustment parameter; and
reading the spectrum, the reaction condition, the theoretical state, the actual state, the default state, the adjustment parameter or at least a combination of the two, performing a big data calculation, operating a controlling unit based the big data calculation, detecting a physic state of the material through the spectrum.

7. A method measuring a physical state of a material by spectrum as mentioned in claim 6, wherein the spectrum is detected from a first action path.

8. A method measuring a physical state of a material by spectrum as mentioned in claim 6, wherein the spectrum is detected from a second action path communicated with a first action path.

9. A method measuring a physical state of a material by spectrum as mentioned in claim 6, wherein the spectrum is detected from a tube communicated with a first action path and a second action path.

10. A method measuring a physical state of a material by spectrum as mentioned in claim 6, further comprising controlling an action condition based on a variation of the spectrum relating to the material to be measured after detecting the spectrum.

11. A method measuring a physical state of a material by spectrum as mentioned in claim 6, wherein at least parts of the material to be measured are in a plasma state.